



-30A, -100V P CHANNEL MOSFET

DESCRIPTION

SVT10500PD is a P channel enhancement mode power MOS field effect transistor which is produced using Silan's LVMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance and high avalanche breakdown tolerance.

This device is widely used in UPS, Power Management for Inverter Systems.

FEATURES

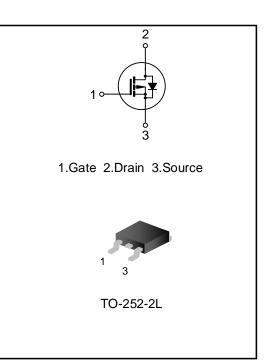
- -30A, -100V, $R_{DS(on)(typ.)} = 35m\Omega@V_{GS} = -10V$
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability
- 100% avalanche tested
- Pb-free lead plating
- RoHS compliant

KEY PERFORMANCE PARAMETERS

| Characteristics | Ratings | Unit |
|-------------------------|-----------|------|
| V _{DS} | -100 | V |
| V _{GS(th)} | -1.5~-2.5 | V |
| R _{DS(on),max} | 50 | mΩ |
| ID | -30 | А |
| Q _{g.typ} | 80 | nC |

ORDERING INFORMATION

| Part No. | Package | Marking | Hazardous Substance Control | Packing Type |
|--------------|-----------|---------|-----------------------------|--------------|
| SVT10500PDTR | TO-252-2L | 10500PD | Halogen free | Tape & Reel |





ABSOLUTE MAXIMUM RATINGS (UNLESS OTHERWISE NOTED, TJ=25°C)

| Characteristics | Sumbol | Test conditions | | Ratings | | l lmit |
|--------------------------------|------------------|--|------|---------|------|--------|
| Unaracteristics | Symbol | Test conditions | Min. | Тур. | Max. | Unit |
| Drain-Source Voltage | V _{DS} | | -100 | | | V |
| Gate-Source Voltage | V _{GS} | | -20 | | 20 | V |
| | | T _C =25°C | | | -30 | А |
| Drain Current | ID | T _C =100°C | | | -20 | А |
| Drain Current Pulsed (Note 1) | I _{DM} | T _C =25°C | | | -120 | А |
| Power Dissipation (Note 2) | PD | T _C =25°C | | | 104 | W |
| Single Buland Avalanaha Energy | E | L=0.5mH, V_{DD} =-80V, R _G =25 Ω , | | | 289 | ~ 1 |
| Single Pulsed Avalanche Energy | E _{AS} | starting temperature T _J =25°C | | | 209 | mJ |
| Single Pulsed Current | I _{AS} | | | | -34 | А |
| Operation Junction | т | | 55 | | 150 | °C |
| Temperature Range | TJ | | -55 | | 150 | °C |
| Storage Temperature Range | T _{stg} | | -55 | | 150 | °C |

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Test conditions | Ratings | | Unit | |
|----------------------------|-------------------|--|---------|------|------|-------|
| Gharacteristics | | | Min. | Тур. | Max. | Unit |
| Thermal Resistance, | Б | | | | 1.2 | °C/W |
| Junction-case, Bottom | R _{θJC} | | | | 1.2 | -0/00 |
| Thermal Resistance, | Р | | | | 62.0 | |
| Junction-ambient | R _{θJA} | | | | 02.0 | °C/W |
| Soldering Temperature(SMD) | T _{sold} | Reflow soldering: 10 ± 1 sec, 3times | | | 260 | °C |



ELECTRICAL CHARACTERISTICS (UNLESS OTHERWISE NOTED, TJ=25°C)

Static characteristics

| Characteristics | Symbol | Test conditions | | Ratings | | Unit |
|--------------------------------|---------------------|--|------|---------|------|------|
| Gharacteristics | Symbol | rest conditions | Min. | Тур. | Max. | Unit |
| Drain-source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =-250µA | -100 | | | V |
| Drain-source Leakage Current | | V _{DS} =-100V, V _{GS} =0V, T _J =25°C | | | -1.0 | |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =-100V, V _{GS} =0V, T _J =125°C | | -1.0 | -10 | μA |
| Gate-source Leakage Current | I _{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | ±100 | nA |
| Gate Threshold Voltage | V _{GS(th)} | V _{GS} =V _{DS} , I _D =-250µA | -1.5 | | -2.5 | V |
| Static Drain-source | P | V _{GS} =-10V, I _D =-15A | | 35 | 50 | ~ |
| On State Resistance | R _{DS(on)} | V _{GS} =-4.5V, I _D =-10A | | 45 | 65 | mΩ |
| Gate Resistance | Rg | f=1MHz | | 12 | | Ω |

Dynamic characteristics

| Characteristics | Sumbol | Test conditions | Test conditions Unit | | | |
|------------------------------|------------------------|--|----------------------|------|------|------|
| Onaracteristics | Symbol Test conditions | | Min. | Тур. | Max. | Onit |
| Input Capacitance | C _{iss} | | | 4440 | | |
| Output Capacitance | C _{oss} | f=1MHz, V _{GS} =0V, V _{DS} =-25V | | 233 | | pF |
| Reverse Transfer Capacitance | C _{rss} | | | 144 | | |
| Turn-on Delay Time | t _{d(on)} | | | 9.8 | | |
| Turn-on Rise Time | tr | V _{DD} =-50V, V _{GS} =-10V, | | 41 | | ns |
| Turn-off Delay Time | t _{d(off)} | R _G =9.1Ω, I _D =-15A (Notes 3, 4) | | 258 | | |
| Turn-off Fall Time | t _f | (NOIES 3, 4) | | 90 | | |
| Total Gate Charge | Qg | | | 80 | | |
| Gate-source Charge | Q _{gs} | V _{DD} =-50V, V _{GS} =-10V, I _D =-15A | | 19 | | nC |
| Gate-drain Charge | Q _{gd} | (Notes 3, 4) | | 15 | | |
| Gate-plateau Voltage | V _{plateau} | | | 4.1 | | V |

Reverse diode characteristics

| Characteristics | Symbol | Test conditions | Ratings | | Unit | |
|---------------------------|------------------------|--|---------|------|------|------|
| onardotenstics | Symbol Test conditions | | Min. | Тур. | Max. | Onic |
| Continuous Source Current | I _S | T _C =25°C, Integral Reverse P-N | | | -30 | ٨ |
| Pulsed Source Current | I _{S,pulse} | Junction Diode in the MOSFET | | | -120 | A |
| Diode Forward Voltage | V _{SD} | I _S =-10A, V _{GS} =0V | | | -1.4 | V |
| Reverse Recovery Time | Trr | I _S =-15A, V _{GS} =0V, | | 31 | | ns |
| Reverse Recovery Charge | Q _{rr} | dIF/dt=100A/µs (Note 3) | | 0.05 | | μC |

Notes:

1. Pulse time 5µs;

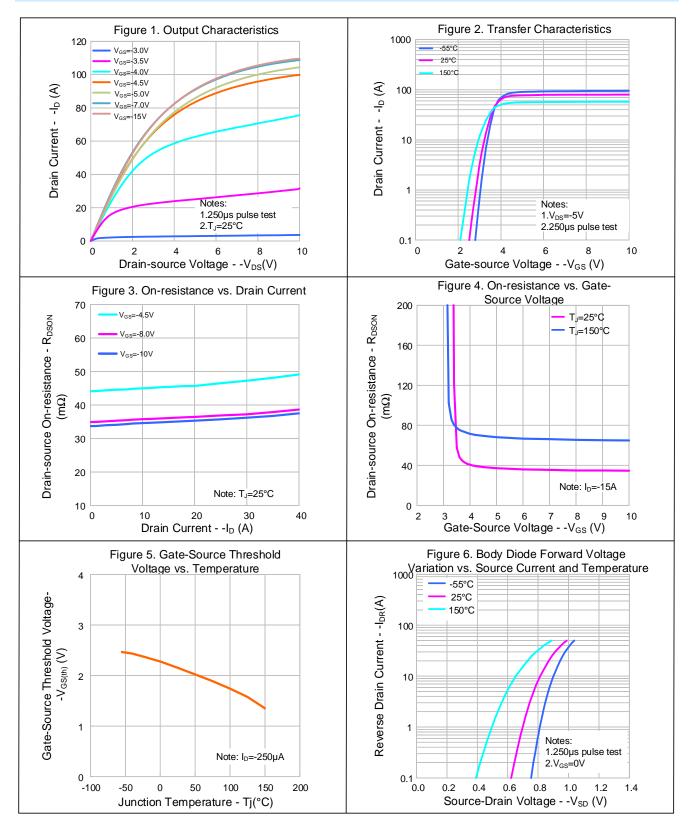
2. The dissipation power will change with temperature, derating above 25°C: 0.83W/°C;

3. Pulse Test: Pulse width ≤300µs, Duty cycle≤2%;

4. Essentially independent of operating temperature.

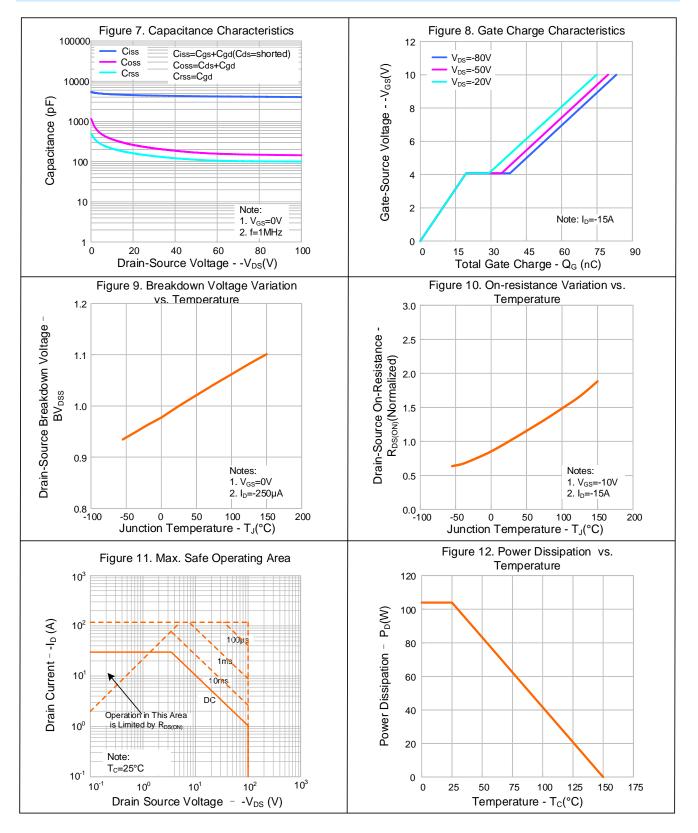


TYPICAL CHARACTERISTICS





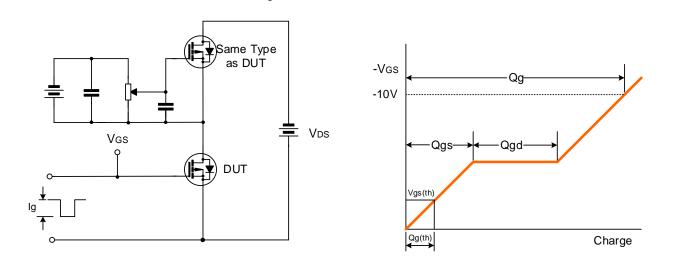
TYPICAL CHARACTERISTICS (CONTINUED)





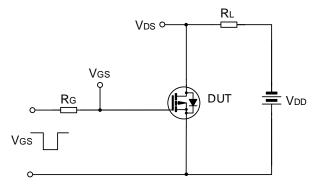


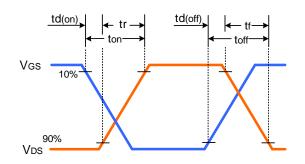
TYPICAL TEST CIRCUIT



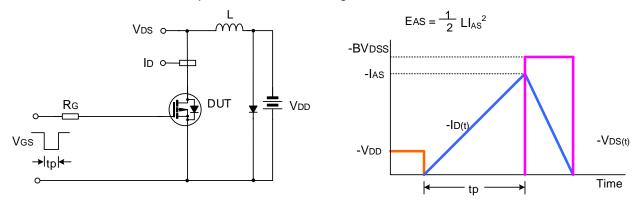
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform



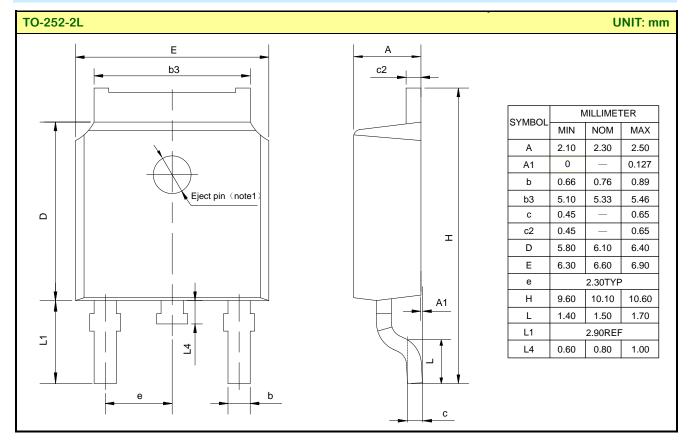


Unclamped Inductive Switching Test Circuit & Waveform





PACKAGE OUTLINE





MOS DEVICES OPERATE NOTES:

Electrostatic charges may exist in many things. Please take following preventive measures to prevent effectively the MOS electric circuit as a result of the damage which is caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic.
- Equipment cases should be earthed.
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.



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